End of Life - Last Available Purchase Date: 11-October-2023 (PTN-OPT-1278-2023-REV-1)



DESCRIPTION

www.vishay.com

Vishay Semiconductors

TSFF5210

High Speed Infrared Emitting Diode, 870 nm, **GaAlAs Double Hetero**



TSFF5210 is an infrared, 870 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and

high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- · Package form: T-1 3/4
- Dimensions (in mm): Ø 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 870 \text{ nm}$
- High reliability
- · High radiant power
- · High radiant intensity
- Angle of half intensity: $\varphi = \pm 10^{\circ}$
- · Low forward voltage
- · Suitable for high pulse current operation
- High modulation bandwidth: f_c = 24 MHz
- · Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Infrared video data transmission between camcorder and TV set
- · Free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	l _e (mW/sr)	φ (°)	λ _p (nm)	t _r (ns)	
TSFF5210	180	± 10	870	15	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSFF5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

Note

· MOQ: minimum order quantity

COMPLIANT HALOGEN

FREE

GREEN

(5-2008)



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ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		١ _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	А	
Power dissipation		Pv	180	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	-40 to +85	°C	
Storage temperature range		T _{stg}	-40 to +100	°C	
Soldering temperature	$t \leq 5 \text{ s}, 2 \text{ mm}$ from case	T _{sd}	260	°C	
Thermal resistance junction to ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	230	K/W	



Fig. 1 - Power Dissipation Limit vs. Ambient Temperature



Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 100 mA, t _p = 20 ms	V _F	-	1.5	1.8	V
	I _F = 1 A, t _p = 100 μs	V _F	-	2.3	3.0	V
Temperature coefficient of V_F	I _F = 1 mA	TK _{VF}	-	-1.8	-	mV/K
Reverse current	V _R = 5 V	I _R	-	-	10	μA
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj	-	125	-	pF
	I _F = 100 mA, t _p = 20 ms	I _e	120	180	360	mW/sr
Radiant intensity	I _F = 1 A, t _p = 100 μs	l _e	-	1800	-	mW/sr
Radiant power	I _F = 100 mA, t _p = 20 ms	фе	-	50	-	mW
Temperature coefficient of ϕ_{e}	I _F = 100 mA	TKø _e	-	-0.35	-	%/K
Angle of half intensity		φ	-	± 10	-	0
Peak wavelength	I _F = 100 mA	λρ	-	870	-	nm
Spectral bandwidth	I _F = 100 mA	Δλ	-	40	-	nm
Temperature coefficient of λ_p	I _F = 100 mA	ΤΚλ _p	-	0.25	-	nm/K
Rise time	I _F = 100 mA	t _r	-	15	-	ns
Fall time	I _F = 100 mA	t _f	-	15	-	ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c	-	24	-	MHz
Virtual source diameter		d	-	3.7	-	mm

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BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)



Fig. 3 - Pulse Forward Current vs. Pulse Duration



Fig. 4 - Forward Current vs. Forward Voltage



Fig. 5 - Radiant Intensity vs. Forward Current



Fig. 6 - Relative Radiant Power vs. Wavelength



Fig. 7 - Relative Radiant Intensity vs. Angular Displacement



Fig. 8 - Attenuation vs. Frequency

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PACKAGE DIMENSIONS in millimeters





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